

25C D ■ 8235605 0004554 0 ■ SIEG T-31-17

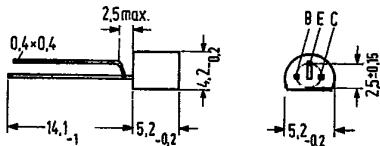
PNP Silicon Planar Transistor

BF 926

SIEMENS AKTIENGESELLSCHAFT 04554 D

BF 926 is an epitaxial PNP silicon planar transistor in TO 92 plastic package (10 A 3 DIN 41868). The transistor is intended for use in VHF oscillator stages, in particular for driving MOS mixer stages.

Type	Ordering code
BF 926	Q62702-F 678



Approx. weight 0.26 g

Dimensions in mm

Maximum ratings

Collector-emitter voltage	$-V_{CEO}$	30	V
Collector-base voltage	$-V_{CBO}$	40	V
Emitter-base voltage	$-V_{EBO}$	4	V
Collector current	$-I_C$	25	mA
Emitter current	$-I_E$	30	mA
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Total power dissipation ($T_{amb} = 45^\circ\text{C}$)	P_{tot}	300	mW

Thermal resistance

Junction to ambient air	R_{thJA}	<350	K/W
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600

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LCL 04555 D

T-31-17
BF 926

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Static characteristics ($T_{amb} = 25^\circ C$)

Collector cutoff current

($-V_{CB} = 20$ V)

$-I_{CBO}$ < 60

nA

Collector-emitter breakdown voltage

($-I_C = 2$ mA)

$-V_{CEO}$ > 30

V

Collector-base breakdown voltage

($-I_C = 10$ μA)

$-V_{CBO}$ > 40

V

Emitter-base breakdown voltage

($-I_E = 10$ μA)

$-V_{EBO}$ > 4

V

DC current gain

($-I_C = 1$ mA; $-V_{CE} = 10$ V)

h_{FE} 80 (> 30)

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Dynamic characteristics ($T_{amb} = 25^\circ C$)

Transition frequency

($-I_C = 5$ mA; $-V_{CE} = 10$ V; $f = 100$ MHz)

f_T 600

MHz

Reverse transfer capacitance

($-V_{CB} = 10$ V; $-I_C = 5$ mA; $f = 1$ MHz)

$-C_{12e}$ 0.6

pF

Output capacitance

($-I_E = 0$; $-V_{CB} = 10$ V; $f = 1$ MHz)

C_{OB} 0.8

pF

Input capacitance

($-V_{EBO} = 0.15$ V; $NF = 1$ MHz)

C_{EBO} 2

pF